

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-212411

(43)Date of publication of application : 04.08.1992

(51)Int.Cl. H01L 21/203
C30B 29/40
H01L 21/205
H01L 21/26

(21)Application number : 03-055267

(71)Applicant : NEC CORP

(22)Date of filing : 20.03.1991

(72)Inventor : SUGAO SHIGEO

(30)Priority

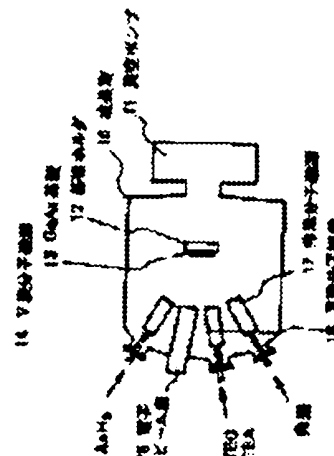
Priority number : 02160105 Priority date : 19.06.1990 Priority country : JP

(54) EPITAXIAL GROWTH METHOD

(57)Abstract:

PURPOSE: To obtain an atomic layer epitaxial growth method capable of forming a selective growth layer having a minute local region less than or equal to 10nm and precision less than or equal to 0.1 μ m.

CONSTITUTION: A GaAs substrate 13 is irradiated with an As beam from a group V molecular beam source 14 and triethyl aluminum TEA from a group III molecular beam source 16, thereby forming an aluminum arsenide layer. Said layer is irradiated with fluorine particles from a fluorine molecular beam source 17, thereby forming an aluminum fluoride (AlF₃) layer, which turns to a selective growth mask. A converged electron beam is projected from an electron beam source 15, fine lines are scanned, images are drawn, chemically adsorbed fluorine atoms are made to leave, and epitaxial growth is activated. After that, an As beam and triethyl gallium TEG molecules are irradiated, thereby growing a gallium arsenide layer only in the part subjected to image drawing by the electron beam.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of

rejection]

[Date of extinction of right]